RECORD EFFICIENT UPCONVERTER SOLAR CELL DEVICES

Jan Christoph Goldschmidt1*, Stefan Fischer2, Barbara Herter3, Benjamin Fröhlich4, Karl W. Krämer5, Bryce S. Richards6, Aruna Ivaturi7, Sean K.W. MacDougall8, Jose Marques-Hueso9, Elena Favilla10, Mauro Tonelli11

1,2,3,4Fraunhofer Institute for Solar Energy Systems, Heidenhofstr. 2, 79110 Freiburg, Germany
5Department of Chemistry and Biochemistry, University of Bern, Freiestrasse 3, 3012 Bern, Switzerland
6Institute of Microstructure Technology (IMT) and Light Technology Institute (LTI), Karlsruhe Institute of Technology, Hermann-von-Helmholtz-Platz 1, 76344 Eggenstein-Leopoldshafen, Germany
7,8,9School of Engineering and Physical Sciences, Heriot-Watt University, Edinburgh, EH14 4AS, Scotland
10,11Dipartimento di Fisica - Universita' di Pisa, Largo B. Pontecorvo, 3, 56127 PISA, Italy

*jan.christoph.goldschmidt@ise.fraunhofer.de

ABSTRACT: In this paper, we give a historic overview over the development of upconverter solar cell devices and show how performance has increased in the past few years. We present measurements of upconverter solar cell devices showing a world-record increase in short-circuit current density due to upconversion of 0.5% relative for a bifacial crystalline silicon solar cell. Finally, we discuss concepts to further increase upconversion performance: photonic structures that combine local irradiance enhancement and resonant emission amplification and spectral concentration to enlarge the utilized spectral range.

Keywords: Upconversion, Antireflection Coating, Silicon Solar Cell, Concentrators, Spectral Conversion

1 INTRODUCTION

For silicon solar cells, 20% of the energy incident from the sun is lost, because sub-bandgap photons cannot generate electron-hole pairs in the silicon. For other emerging solar cell technologies with higher bandgaps, such as GaAs or perovskite solar cells, these losses are considerably higher, with 34% and 39%, respectively being lost. Upconversion – the generation of one high-energy photon out of at least two low-energy photons – can reduce these losses. Despite theoretical limits close to 40% for ideal silicon solar cells with attached upconverters [1, 2] real devices stayed far below those values [3-6]. While the early works performed experiments with monochromatic excitation, upconversion has been increasingly investigated under broad-spectrum illumination to determine its potential for solar energy harvesting and efficiencies have increased considerably [7-10]. In this paper, we give an overview of the historic developments in the field of upconverter solar cell devices. Then, we present our measurement results, which constitute new record performances for upconverter solar cell devices. Finally, we discuss how upconversion performance can be further increased with photonic structures and spectral concentration.

2 HISTORIC DEVELOPMENT

As summarized in [20], the first proof-of-concept upconverter solar cell device was realized by Gibart et al. in 1996, who attached an trivalent erbium (Er3+) and trivalent ytterbium (Yb3+) co-doped vitroceramic to a gallium arsenide (GaAs) solar cell [11]. In 2005, Shalav et al. were the first to apply a β-NaYF4: 20% Er3+ upconverter to a bifacial silicon solar cell [3]. The upconversion in Er3+, which is beneficial for silicon solar cells, occurs mainly via ground state absorption, energy transfer between two excited ions (donor → acceptor) and subsequent spontaneous emission of a high energy photon. Under excitation at 1523 nm the dominant upconversion emission is at 980 nm. Other relevant processes are multi-photon relaxation and - to a limited extent - excited state absorption.

In 2007, Shalav et al. reported an external quantum efficiency (EQE) of the combined silicon solar cell upconverter systems of 3.4% under monochromatic excitation with a laser wavelength of 1523 nm and an irradiance of 24000 W/m2 [12]. Typically, the upconversion quantum yield and therefore the EQE due to upconversion of sub-bandgap photons increase with the irradiance. To facilitate the comparison for values determined at different irradiances, the EQE can be normalized to the irradiance [13]. The values published by Shalav et al correspond to a normalized EQE of 0.014 cm²W⁻¹. In 2010, Fischer et al. reported an EQE of 0.34% (1090 W/m² at 1523 nm) equivalent to a normalized EQE of 0.03 cm²W⁻¹ [5]. Most of the analyses have been carried out under monochromatic excitation [3, 5, 11, 12, 14-16], while for the application...
in photovoltaics broad-band illumination is relevant. The first experiments applying broad-band illumination on upconverter solar cell devices were reported by Goldschmidt et al. in 2011. An EQE of 0.81% under broad-band excitation with a photon-flux equivalent to 458 suns was achieved [7]. Since then, the material quality has been improved and the utilized solar cells were customized for the application of upconverters [17]. In Ref. [10], Fischer et al. reported an average EQE of 0.69% in the spectral region of 1450 – 1600 nm at 78 suns concentration (equivalent to a normalized EQE of 0.03 cm²W⁻¹) for β-NaYF₄: 25% Er³⁺ embedded in the polymer perfluorocyclobutyl (PFCB) with a powder to polymer concentration of 75.7 w/w%. Using the pure upconverter material β-NaYF₄: 25% Er³⁺, which was filled into a powder cell and attached to the back of an optimized solar cell, an even higher EQE of 1.28% at 77 suns (0.05 cm²W⁻¹) was achieved [9].

For sun-like illumination, an average EQE value for a certain spectral region is not a very meaningful figure-of-merit. Instead it is more interesting to know, how much additional current can be generated due to upconversion under illumination with the full solar spectrum onto the upconverter solar cell device. In Ref [10] Fischer et al. reported an additional short-circuit current density due to upconversion of 13.1 mA/cm² for an upconverter silicon solar cell device using a solar concentration of 210 suns. The used upconverter material was β-NaYF₄: 25% Er³⁺ embedded in PFCB. The increase in short-circuit current density constitutes a relative increase of the solar cell’s short-circuit current density of 0.19%. This is more than a magnitude higher than the value of 0.014% achieved three years earlier [7].

2 DEVICE MEASUREMENTS

Approach

The microcrystalline upconverter materials β-NaYF₄: 25% Er³⁺ and Gd₂O₂S: 10% Er³⁺ were embedded in PFCB with 84.9 w/w% concentration [6], and nano-crystalline samples of BaY₂F₈: 30% Er³⁺ [18] were attached with an index matching liquid to the rear side of planar bifacial crystalline silicon solar cells that featured broad-band anti-reflection coatings [17]. The created upconverter solar cell devices were characterized using concentrated light of a solar simulator. The incident light was concentrated with a Fresnel lens and the concentration level adjusted by the height of the lens above the device. To facilitate the detection of the upconversion signal, photons with energies above the bandgap were blocked from reaching the solar cell. The measurements were performed with the upconverter material and un-doped references containing no erbium attached to the solar cells. The difference of the two determined short-circuit current densities results in the additional short-circuit current density due to upconversion ∆j_SC,UC. A spectral mismatch correction [9] was applied to the results.

Results

As reported in [19], we determined a maximum additional short-circuit current density due to upconversion ∆j_SC,UC of 17.2±3.0 mA/cm² at illumination with 94±17 suns for an upconverter solar cell device with an nano-crystalline BaY₂F₈: 30% Er³⁺ upconverter. This translates into a record relative enhancement of 0.55±0.14%, considering the 33.4 mA/cm² short-circuit current density of the used silicon solar cell with 17.6% efficiency. A ∆j_SC,UC of 8.1±0.7 mA/cm² at 70±6 suns and 5.3±0.5 mA/cm² at 67±6 suns were achieved with the micro-crystalline upconverter materials β-NaYF₄: 25% Er³⁺ and Gd₂O₂S: 10% Er³⁺, respectively. These values demonstrate the huge progress that has been made in the last years and constitute a nearly 40 fold increase compared to the only 3 year old best values [7].

Despite the promising progress in the last years, further means to increase upconverter solar cell device performance are necessary, to make upconversion really relevant for photovoltaics. One can distinguish between concepts that enhance the actual process of upconversion and concepts that enlarge the utilized spectral range.

Photonics and external concentration

As we have already summarized in [20], one approach to enhance the upconversion process is to use plasmonic or dielectric photonic structures to a) increase the local irradiance on the upconverter and b) modify the local density of photon states to enhance wanted radiative emission processes and suppress the unwanted [21, 22]. An enhancement of upconversion luminescence by a factor of 3.8 was found in experiments for a single Er³⁺ and Yb³⁺ co-doped upconverter nanoparticle placed at an optimized position in proximity to a gold nanoparticle [23]. Theoretical analyses showed local enhancement factors of the same magnitude, but no significant enhancement averaged over the volume around the metal nanoparticle [24, 25]. The presence of the metal nanoparticle introduces new non-radiative loss processes that may override any positive effects. Dielectric nanostructures, however, are more promising, as they show lower parasitic absorption. In this field, work has concentrated mainly on enhancing the photoluminescence of erbium at a wavelength of 1530 nm (no upconversion). There are less works on the enhancement of
upconversion luminescence. Niu et al. reported a 27-fold increase for the emission at around 660 nm under excitation at 980 nm for $\beta$-NaYF$_4$:Er$^{3+}$ nanoparticles coated on top of an opal photonic crystal [26]. Johnson et al. reported a 6-fold increase for the dominant erbium upconversion emission at 980 nm for $\beta$-NaYF$_4$:Er$^{3+}$ nanoparticles embedded into a Bragg stack consisting of 30 bilayers [27].

Furthermore, there are only very few theoretical works investigating the effects of dielectric photonic structures on upconversion that take into account all relevant effects, which are the increased irradiance, the changed local density of photon states, and the internal dynamics of the upconverter [28]. In such a complete analysis [29], investigating the effect of a grating structure, we could show that upconversion luminescence could be increased in average by a factor of 3.0 compared to an unstructured references, while the upconversion quantum yield could be increased by an average factor of 1.5.

Another concept is to use external concentration onto the upconverter to exploit the non-linearity of the upconversion process, which results into higher upconversion quantum yields at higher excitation. Here, it is especially promising to place the concentrator between the solar cell and the upconverter, such that each element can be operated at its optimum concentration level (which usually lower for the silicon solar cell than for the upconverter) [30].

Spectral concentration

The absorption range of the rare-earth ions, where photons can be converted to higher energies, is rather narrow. Typically, Er$^{3+}$-based upconverter materials feature an absorption range from roughly 1480 nm to 1580 nm. This limited spectral range can be extended by either co-doping of a sensitizer, or by the use of a second luminescent material that absorbs in a wide spectral range and emits in the absorption range of the upconverter [31, 32]. The use of a second luminescent material has the advantage that additional to the larger used spectral range, also the photon flux in the absorption range of the upconverter is enhanced, which then leads to higher upconversion quantum yields. Because a larger spectral region is funnelled into the narrow spectral region where the upconverter is active, this process is also called spectral concentration [31, 32]. Assuming an upconversion quantum yield of 17% (a value that should be attainable with good material at high concentration), about 0.5 mA/cm$^2$ could be generated by an upconverter material that is active in the spectral range from 1480 to 1580 nm, such as Er$^{3+}$. Assuming that the photons between the bandgap of silicon and 1480 nm could be shifted to the absorption range of the upconverter with an efficiency of 80% and again assuming 17% quantum yield for the upconversion results into 1.2 mA/cm$^2$ that could be gained by the spectral concentration and an overall 1.7 mA/cm$^2$ that could be achieved by upconversion and spectral concentration under 1 sun illumination. This would translate in a roughly 4% relative efficiency gain for a good silicon solar cell. However, for higher bandgap solar cells the potential gains and also the relative impact due to the current enhancements are more substantial. This is also true in the context of silicon based tandem solar cells, where the overall current is lower – usually limited by the silicon solar cell – and therefore significantly higher relative gains could be expected.

4 SUMMARY

The performance of upconverter solar cell devices has increased considerably in the past few years. Recently a new record value of 17.0±3.0 mA/cm$^2$ additional short-circuit current density due to upconversion of sub-bandgap photons for a sun-like illumination with 94±17 suns was achieved, for an upconverter solar cell device consisting of an bifacial crystalline silicon solar cell and a mono-crystalline BaY$_2$F$_8$: 30% Er$^{3+}$ upconverter [19]. This translates into a record relative enhancement of 0.55±0.14%, considering the 33.4 mA/cm$^2$ short-circuit current density of the used silicon solar cell. These values constitute a nearly 40 fold increase compared to the only 3 year old best values. To further increase the upconversion performance, photonic structures could be applied, for instance. Theoretical analyses show that a grating structure could increase the upconversion quantum yield by a factor of 1.5. Furthermore, spectral concentration, the downshifting of photons with energies between the bandgap of the solar cell and the active region of the upconverter into the active region of the upconverter, could more than triple upconverter performance.

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